

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-12. (Canceled)

13. (Currently Amended) Compliant substrate according to claim 35, ~~characterized in that~~
wherein said bonding interface is an interface resulting from a surface preparation and/or an
interface resulting from a heat treatment and/or an interface resulting from a creation of defects.

14. (Currently Amended) Compliant substrate according to claim 13, ~~characterized in that~~
wherein said surface preparation is a control of roughness and/or hydrophylia.

15. (Currently Amended) Compliant substrate according to Claim 35 ~~[[13]]~~, ~~characterized in~~
~~that where~~ said ~~bonding interface~~ structure also comprises at least one intermediate layer between
the thin layer and the carrier.

16. (Currently Amended) Compliant substrate according to claim 15, ~~characterized in that~~
wherein the intermediate layer is a metal layer or metal alloy layer.

17. (Currently Amended) Compliant substrate according to claim 15, ~~characterized in that~~ wherein said at least one intermediate layer is formed such that it comprises non-homogeneities.

18-34. (Canceled)

35. (Currently Amended) Compliant substrate comprising a carrier and a structure comprising at least one thin layer ~~[[formed]], the structure being on [[the]]~~ a surface of said carrier, the carrier and the ~~[[thin layer]]~~ structure being joined one to another by a bonding interface whose bonding energy is controlled to permit absorption, in whole or in part by ~~the thin layer and/or~~ the bonding interface, of stresses brought to said compliant substrate.

36-50. (Canceled)

51. (Previously Presented) Compliant substrate according to claim 35, wherein said stresses are brought by a hetero-epitaxial growth realized on the thin layer.

52. (New) Compliant substrate according to claim 35, wherein the carrier comprises at least one intermediate layer formed or transferred on the surface of said carrier, the bonding interface being located between said structure and said at least one intermediate layer formed or transferred on the surface of said carrier.

53. (New) Compliant substrate according to claim 15, wherein said at least one intermediate layer is a layer formed or transferred on the thin layer.